WHAT IS CLAIMED IS:

1	1. A substrate processing chamber comprising:			
2	a chamber body;			
3	a chamber top disposed on the chamber body; and			
4	a transformer-coupled plasma generator plate within the substrate			
5	processing chamber having a plurality of transformer cores within the transformer-			
6	coupled plasma generator plate and a plurality of through holes forming conduits from			
7	a first side of the transformer-coupled plasma generator plate to a second side of the			
8	transformer-coupled plasma generator plate, a first conduit passing through a first			
9	transformer core.			
1	2. The substrate processing chamber of claim 1 further comprising			
2	a second conduit not passing through a transformer core.			
ĺ	3. The substrate processing chamber of claim 1 wherein the plasma			
2	generator plate is flat.			
1	4. The substrate processing chamber of claim 1 further comprising			
2	a second transformer core within the transformer-coupled plasma generating plate, a			
3	first primary coil being disposed to electro-magnetically couple to the first transformer			
Ą	core and a second primary coil being disposed to electro-magnetically couple to the			
5	second transformer core, wherein the first primary coil and the second primary coil are			
6	connected to each other in series.			
ĵ	5. The substrate processing chamber of claim 1 wherein the toroidal			
2	transformer core comprises ferrite material.			
1	6. The substrate processing chamber of claim 1 wherein the			
2	transformer-coupled plasma generator plate includes a dielectric spacer between the			
3	first side and the second side, and a remainder of an outer surface of the generator plate			
4	comprises an electrical conductor.			
1	7. The substrate processing chamber of claim 6 wherein the			
2	dielectric spacer is disposed within a conduit through the transformer-coupled generate			
3	plate.			

Ä.	8. The substrate processing chamber of claim 1 further comprising			
2	an alternating-current power supply configured to operate at a frequency of about			
3	1 KHz-2 MHz.			
1	9. A substrate processing chamber comprising:			
2	a chamber body;			
3	a chamber top disposed on the chamber body;			
4	an alternating-current power supply; and			
5	a transformer-coupled plasma generator plate having a plurality of			
6	through holes forming conduits from a first side of the transformer-coupled plasma			
7	generator plate within the substrate processing chamber to a second side of the			
8	transformer-coupled plasma generator plate within the substrate processing chamber, a			
9	first portion of the conduits passing through centers of a plurality of toroidal			
10	transformer cores within the generator plate and a second portion of the conduits not			
1	passing through centers of transformer cores, the generator having a first surface			
12	comprising metal, a second surface comprising metal, and a plurality of dielectric			
13	spacers disposed between the first surface and the second surface in each of the first			
14	portion of the conduits.			
1	10. A plasma generator plate comprising:			
2	a first side;			
3	a second side;			
4	a first conduit passing from the first side to the second side through a			
5	first transformer core within the plasma generator plate;			
6	a second conduit passing from the first side to the second side through a			
7	second transformer core.			
1	11. The plasma generator plate of claim 10 further comprising a first			
2	dielectric spacer in a first secondary current path around the first transformer core.			
1	12. A method of processing a substrate in a plasma processing			
2	system, the method comprising:			
3	providing a substrate to a substrate holder in a processing chamber of the			
4	plasma processing system;			

flowing a plasma precursor into a multi-core transformer-coupled		
plasma generator;		
generating a plasma from the plasma precursor with the multi-core		
transformer coupled plasma generator; and		
processing the substrate.		
13. The method of claim 12 wherein the multi-core transformer-		
coupled plasma generator is within the processing chamber.		
coupled plasma generator is within the processing chamber.		
14. The method of claim 13 wherein the multi-core transformer-		
coupled plasma generator is a generator plate comprising a plurality of transformer		
cores within the generator plate and a plurality of through-holes forming conduits from		
a first side of the generator plate to a second side of the generator plate.		
15. The method of claim 12 wherein plasma formed by the multi-		
core transformer-coupled plasma generator is coupled to the processing chamber		
through a conduit.		
16. The method of claim 15 wherein the multi-core transformer-		
coupled plasma generator has a first conduit passing through a first transformer core		
and through a second transformer core.		
17. The method of claim 15 wherein the multi-core transformer-		
coupled plasma generator has a first conduit passing through a first transformer core		
and a second conduit passing through a second transformer core.		
18. A plasma processing system comprising:		
a first substrate support structure configured to hold a first substrate in		
processing chamber;		
a second substrate support structure configured to hold a second		
substrate in the processing chamber; and		
a transformer-coupled plasma generator within the processing chamber		
disposed between the first substrate support structure and the second substrate support		

I	19. The plasma processing system of claim 18 wherein the		
2	transformer-coupled plasma generator includes a toroidal transformer core.		
1	20. The plasma processing system of claim 18 wherein the plasma		
2	generator comprises a plasma generating plate having a plurality of transformer cores		
3	within the plasma generating plate and a plurality of through holes forming conduits		
4	from a first side of the plate to a second side of the plate.		
•	nom a mot side of the place to a second side of the place.		
1	21. A method of simultaneously processing substrates in a plasma		
2 .	processing system, the method comprising:		
3	providing a first wafer and a second wafer to a processing chamber;		
4	flowing plasma precursor into the chamber;		
5	generating a plasma with a transformer-coupled plasma generator		
6	disposed between the first wafer and the second wafer; and		
7	simultaneously processing the first wafer and the second wafer.		
1	22. A plasma generator comprising:		
2	an inlet in fluid communication with;		
3	a first conduit passing through		
4	a first toroidal transformer core and through		
5	a second toroidal transformer core;		
6	a second conduit completing a plasma current circuit, in cooperation		
7	with the first conduit, around the first toroidal transformer core and around the second		
8	toroidal transformer core; and		
9	an outlet in fluid communication with the first conduit.		
1	23. A plasma generator comprising:		
2	an inlet in fluid communication with		
3	a first conduit passing through a first transformer core and with		
4	a second conduit passing through a second transformer core;		
5	a third conduit in fluid communication with the first conduit to complete		
6	a first plasma current circuit around the first transformer and in fluid communication		
7	with the second conduit to complete a second plasma current circuit around the second		
8	transformer; and		

9	an outlet in fluid communication with at least the first conduit and the				
10	second conduit.				
1	24. A substrate processing system comprising:				
2	a process chamber with a chamber inlet;				
3	a chamber exhaust; and				
4	a transformer-coupled plasma generator having a first core,				
5	a first conduit passing through the first core,				
6	a second core,				
7	a second conduit passing through the second core, and				
8	a third conduit in fluid communication with the first conduit and				
9	the second conduit to complete a plasma current circuit path through the process				
10	chamber.				
1.	25. The substrate processing system of claim 24 wherein the third				
2	conduit is a center conduit completing a first plasma current circuit path around the firs				
3	core through the process chamber and the first conduit and completing a second plasma				
4	current circuit path around the second core through the process chamber and the second				
5	conduit.				
ĺ	26. The substrate processing system of claim 24 wherein the first				
2	conduit and the second conduit comprise metal and further comprising a dielectric				
3	spacer in the plasma current circuit path.				
1	27. The substrate processing system of claim 24 further comprising:				
2	a fourth conduit passing through				
3	a third core; and				
4	a fifth conduit passing through				
5	a fourth core.				
1	28. The substrate processing system of claim 24 further comprising:				
2	a first primary coil disposed to couple electro-magnetic energy to the				
3	first core;				
4	a second primary coil disposed to couple electro-magnetic energy to the				
5	second core;				

O	a tillid primary con disposed to couple electro-magnetic energy to the			
7	third core;			
8	a fourth primary coil disposed to couple electro-magnetic energy to the			
9	fourth core, wherein the first primary coil, the second primary coil, the third primary			
10	coil, and the forth primary coil are coupled to an AC power supply.			
1	The substrate processing system of claim 28 vyhoroin the first			
1	29. The substrate processing system of claim 28 wherein the first			
2	primary coil, the second primary coil, the third primary coil, and the fourth primary coil			
3	are connected in series with the AC power supply.			
1	30. The substrate processing system of claim 28 wherein the first			
2	primary coil, the second primary coil, the third primary coil, and the fourth primary coil			
3	are connected in parallel to the AC power supply.			
î	31. A plasma generator comprising:			
2	an inlet configured to receive a plasma precursor, the inlet in fluid			
3	communication with a first plasma current path and with a second plasma current path;			
4	a first conduit passing through			
5	a first transformer core;			
6	a second conduit passing through			
7	a second transformer core, wherein the first conduit is essentially co-			
8	linear with the second conduit.			
1	32. A plasma generator comprising:			
2	an outer shell surrounding a first inner shell housing a first toroidal			
3	transformer core; and			
4	a second inner shell housing a second toroidal transformer core, wherein			
5	the first toroidal transformer core and the second toroidal transformer core are dispose			
6	along a common center axis.			
1	33. The plasma generator of claim 32 wherein the first inner shell is			
2	supported within the outer shell by a web allowing circulation of secondary plasma			
3	current around the first inner shell within the outer shell.			

1		34.	The plasma generator of claim 33 wherein the web contains an
2	electrical lead connected to a primary coil disposed to couple electro-magnetic energy		
3	to the first toroidal transformer core.		
1		35.	The plasma generator of claim 32 wherein the first inner shell
2	includes a sha	ped bo	ttom portion to provide a circular cross-section to the inner shell.
1	٠.,	36.	The plasma generator of claim 32 further comprising:
2		an inl	et; and
3		an ou	tlet, both the inlet and the outlet lying along the common center
4	axis.		
1		37.	An ion implantation system comprising:
2		an ior	source having a toroidal plasma generator, and
3		an ior	source aperture aligned essentially along a center line of the
4	toroidal plasma generator.		
1		38.	The ion implantation system of claim 37 further comprising a
2	first extraction	n electr	ode disposed to accelerate ions from the ion source toward a
3	second extrac	tion ele	ectrode.
1.		39.	The ion implantation system of claim 37 wherein the toroidal
2	plasma generator includes a first core and a second core, the first core and the second		
3.	core being ali	gned es	ssentially along a center line of the toroidal plasma generator.
1		40.	A method of providing ions to an ion implantation system, the
2	method comp	rising:	
3		provi	ding an ion precursor to a transformer-coupled toroidal plasma
4	generator in a	n ion s	ource;
5		ionizi	ng at least a portion of the ion precursor into ions, the ions having
6	a greater density at a center of the transformer-coupled toroidal plasma generator and		
7	extending along a line through the center of the transformer-coupled toroidal plasma		
8	generator; and	d	
9		eiecti	ng a portion of the ions out of the ion source.

ī	41. A plasma tolen head comprising.			
2	an outer nozzle;			
3	an inner nozzle, the inner nozzle including a conduit passing through the			
4	inner nozzle from an inlet side toward an outlet,			
5	a toroidal transformer core surrounding the conduit; and			
6	a bypass providing a return path for a secondary plasma current circuit			
7	around the toroidal transformer core.			
	42. The plasma torch head of claim 41 wherein the inner nozzle			
1	-			
2	comprises metal and further including a dielectric spacer in the inner nozzle to preven			
3	an electric path through the inner nozzle around the toroidal transformer core.			
1	43. The plasma torch head of claim 41 wherein a first gas is flown			
2	through the conduit and a second gas if flown through the bypass, the first gas being			
3	different from the second gas.			
	The state of the s			
1	44. The plasma torch head of claim 43 wherein the first gas is			
2	oxygen and the second gas is either propane or hydrogen.			
1	45. The plasma torch head of claim 41 further comprising a primar			
2	coil disposed to couple electro-magnetic energy to the toroidal transformer core			
3	wherein the primary coil and the toroidal transformer core are enclosed within the im-			
4	nozzle.			
;	e to the experience and we have a more than to represent a progress and the progress of the first of the control of the contro			
1	46. A method of cutting material using a plasma torch, the method			
2	comprising:			
3	flowing a plasma precursor in a conduit through a center of a toroidal			
4	transformer core of a plasma generator in an inner nozzle of a plasma torch;			
5	forming plasma from the plasma precursor;			
6	completing a plasma current secondary circuit around the toroidal			
7	transformer core through a bypass; and			
8	transporting plasma out an outlet of the plasma torch.			
1	47. The method of claim 46 further comprising flowing carrier gas			
2	through the bypass.			

1		48.	The method of claim 46 wherein the forming plasma step
2	includes prov	iding a	primary voltage to a primary coil coupling electro-magnetic
3	energy to the toroidal transformer core, the primary voltage being an alternating-current		
4	voltage less th	han abo	out 115 Volts.
1		49.	An ion source for an ion milling apparatus, the ion source
2	comprising:		
3	1 3	a tran	sformer-coupled toroidal plasma generator (having a primary coil
4	disposed to co	•	lectro-magnetic energy to a toroidal core, the transformer-coupled
5	toroidal plasma generator disposed to provide plasma along a center line of the		
6	transformer-c	oupled	toroidal plasma generator toward an accelerator plate.
1		50.	The ion source of claim 1 wherein the transformer-coupled
2	toroidal plasm	na gene	erator further includes a second toroidal core.
1	·	51.	A method for providing ions to an ion milling apparatus, the
2	method comp	rising:	·
3	•	provi	ding an ion precursor to a transformer-coupled toroidal plasma
4	generator;		
5		ionizi	ng at least a portion of the ion precursor to form ions, the ions
6	being concen	trated a	long a center axis of the transformer-coupled toroidal plasma
7	generator; an	d	
8	ments, while appropriate	ejecti	on a portion of the ions toward an accelerator plate.
1		52.	The method of claim 51 wherein the ion precursor forms reactive
2	ions.		•